

Serial No.: Rule 1.53(b) Divisional  
of Serial No. 09/700,132 filed 11/9/00

IN THE SPECIFICATION:

Page 1, after the Title, please insert the following new paragraph:

This application is a divisional application of Serial No.  
09/700,132 filed November 9, 2000, now allowed. *Patent No. 6,624,473*

Page 19, second paragraph, please amend as follows:

In this group of the inventions, in particular, in addition to the third group of the inventions, Ti or Zi-Zr film with excellent hydrogen absorption capacity is formed beforehand on the upper surface of the polycrystalline semiconductor after once removing the gate insulator in order to prevent, as far as possible, the hydrogen from diluting the impurities at the time of their injection from penetrating into the polycrystalline semiconductor.